INTRODUCTION

45-nm-NODE semiconductor devices are being produced worldwide and 32-nm-node processes are being developed. Hitachi has developed excellent dry-etching equipment and processes that can achieve high throughput, high yield, and high productivity in the manufacture of these complex devices.

Dry etching is a chemical reaction between semiconductor-wafer surface materials and reactive gases within the plasma. Photo-resist materials create patterns on semiconductor wafers during the lithography process and serve to protect areas where reactions are not required. The lithography process actually creates feature sizes (patterns) that are smaller than the exposure wavelength (193 nm for ArF excimer exposure) used to create these patterns for leading-edge semiconductor devices. Therefore, many technologies to enhance resolution have been widely applied that often have an adverse impact on dry etching. Dry-etching technologies must not only overcome the negative impact on enhancing resolution, but also improve patterning accuracy.

New concerns regarding yield-related issues are already being seen in addition to typical concerns regarding manufacturing variations in 45–32-nm nodes. The reason is that even very small variations from the CD (critical dimension) or taper angle within a 300-mm wafer may have a large impact on final yields. This situation is conspicuous in 65-nm nodes or less and thus strict targets for uniformity are required by the end users of equipment. Improvements to productivity on the other hand, that have driven down wafer costs are also serious issues. Fig. 1 outlines tactics used for increasing productivity. Equipment productivity clearly plays a major role in decreasing costs. However, the major index, OEE
accomplished by applying coaxially installed turbo molecular pumps, symmetrically designed electrodes, and specially designed variable conductance valves to a completely symmetrical reaction chamber, as shown in Fig. 3. Etching can be improved to have the required symmetrical distribution using this design.

High-volume exhaust systems and low-pressure reactions, which are possible using a high-frequency discharge mechanism with electromagnetic coils, will be used to reduce the influence of disturbing factors in the next step.

Appropriate tuning knobs with features below were introduced to this new concept for dry-etching equipment.

(1) Source power and coil current for incident ion distribution
(2) A two-directional and concentration-controlled gas flow system for radical distribution
(3) Control of the slope of wafer temperature for the
Patterns within 300-mm-diameter wafers. The independent tuning knobs on Hitachi’s dry etching equipment can control the reaction position-by-position and can easily achieve excellent CDU. ECR (electron cyclotron resonance) technology can control absorption distribution of reaction byproducts.

Approaches to stabilizing equipment are often different for users, and thus hardware, processes, and software solutions need to be well balanced.

Two functions are necessary to maintain the stability of equipment and processes. We need to:
(1) Verify the proper functionality of all equipment actuators through feedback, and
(2) Monitor and control the process stability of all chambers based on the reaction model.

Function (1) is easily achieved because root-cause problems are directly indicated by errors. Function (2) is difficult to directly identify, on the other hand, because errors originate from complex root causes and disturbance factors. Therefore, new processes such as AEC and APC gradually become more effective through development from the design of basic to more complex equipment.

GATE PROCESS APPLICATIONS

Gate processes pose numerous challenges in beyond 45-nm-node devices, e.g., in metal gate materials, high-$k$ dielectric materials, immersion photo resists, and drastic reductions in CDU (critical dimension uniformity). These are the next device requirements.

Pattern Sidewall Smoothing

Photo-resist patterns in present immersion-type lithography have greater roughness characteristics than those permitted by device requirements. This roughness is called LWR (line width roughness). LWR should be reduced to values of 4 nm or less in dry-etching processes. Hitachi has developed several methods of reducing LWR, as outlined in Fig. 4. The vertical line indicates the degree of LWR and the horizontal line shows the CD shift from the original. The results for the coating 1 method were based on trimming after fluorocarbon was deposited and those for coating 2 were based on trimming after bromine-containing materials were deposited. These two methods were selected from CD requirements and achieved 3.2-nm LWR. A new curing process was also developed without trimming for zero CD shift. Fig. 5 shows the excellent results obtained with the new curing process.

Excellent CD Uniformity and Low Isolation-dense Bias

High-yield manufacturing not only requires high CDU, but also less bias between isolation and dense patterns within 300-mm-diameter wafers. The independent tuning knobs on Hitachi’s dry etching equipment can control the reaction position-by-position and can easily achieve excellent CDU. ECR (electron cyclotron resonance) technology can control...
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Ions and radicals independently for low isolation-dense bias and can work well in very low-pressure regions where the ion path is quite straight. The CD shift/I-D (isolation-dense) bias dependence on pressure is plotted in Fig. 6. CDU values of 1.8 nm and I-D bias values of 1.0 nm were achieved by using these low-pressure conditions. Hitachi intends to develop the further low-pressure reactions for the 22-nm node and below.

Ultra Low Damage on Photo-resist Patterns

The physical gate length should be less than 20 nm in high-speed devices. As this dimension is much smaller than the limit in current lithography, it is necessary to trim the photo-resist patterns a great deal. Trimmed patterns generally topple over easily or bend because of the lack of adhesion between the photo-resist and underlying materials. Low-speed gas injection and low chamber deposition are utilized to prevent this phenomenon. Fig. 7 shows the results of trimming patterns. Hitachi has excellent 20-nm patterns that were thought to be impossible.

Metal and High-k Materials Etch

Low pressure reaction, one of the ECR technology merits, shows excellent advantages in the reaction of low vapor pressure materials, because materials that can be etched at high pressure and high temperature (around 100°C) can be etched at room temperature in the low pressure regime. This tendency has been demonstrated in chemical-reaction simulations and actual experiments. Low temperatures very effectively improve TDDB (time dependent dielectric breakdown).

DIELECTRIC MATERIAL ETCHING APPLICATIONS

Special requirements for all etching-process characteristics are very important in the dry etching of dielectric materials in addition to low COO (cost of ownership) and COC (cost of consumables). Hitachi developed a new reactor and a new dry etching system, the U-8250, which can be used over wide pressure and bias-power ranges, as shown in Fig. 8. It features various unique hardware functions and enables highly uniform conditions to be easily and independently set up. Four etching chambers can be installed on the U-8250.

Examples of Damascene Process

High-speed logic manufacturing processes require ten or more sets of Cu DD (dual damascene) levels, based on low-resistive Cu and low-k dielectrics. Low COO, contact-hole shrink characteristics, and low damage to porous dielectric materials are a necessity for the via and trench etches of DD. Low COO is achieved by a 4-chamber system and a unique ECP.
(electrically confined plasma) technology, which decreases the deposition of byproducts on the chamber wall during etching and increases the speed at which deposition materials can be removed during cleaning. Other aspects, such as the amount of shrinkage or damage, are minimized by the etch conditions. To date, 25-nm contact hole shrinkage has been demonstrated.

Examples of Metal Hard Mask Etch

It is becoming necessary to study and utilize hard-mask processes as metallization layers and the via and trench feature sizes of the lower damascene layer near the actual device become increasingly smaller and plasma radiation or resist stripping causes critical damage to low-\(k\) materials. There is an example of the process flow in Fig. 9. In-situ single-chamber etching from (1) to (5) in Fig. 9 is possible due to the wide plasma window of the U-8250. This drastically reduces COO.

Examples of Multilayer Mask Etching

The mask structures for FEOL (front end of line) dry etching became more complex and require hard-mask materials due to the reduced photo-resist thickness and weak resistance to etching of new short-wavelength lithography materials, as shown in Fig. 10. These complex mask structures lead to higher COO. Therefore, high-speed etching of mask layers is required along with excellent etching characteristics. Hitachi developed a new process chemistry that simultaneously achieves etching rates of 300 nm/min, with CD shift of <5.0 nm, and CDU of 3 nm based on the above hardware.
taper angle, selectivity, amount of notching, and the trimming rate. Quick process setups and etching performance checks are easily executed based on this MVA model.

EPD Technology

Even if the equipment itself is stable, it is possible for wafers to have some variations. EPD was also redesigned to maintain precise control for this reason. Hitachi reduced the minimum detection limit of exposed area to 2% and the detection delay to 0.2 s.

CONCLUSIONS

Excellent dry-etching processes and equipment for 45-nm-node and below semiconductor manufacturing were studied and established by Hitachi.

REFERENCES


ABOUT THE AUTHORS

Hiromichi Enami

Joined Hitachi, Ltd. in 1978, and now works at the Etching Process Design Department, Kasado Division, Nanotechnology Products Business Group, Hitachi High-Technologies Corporation. He is currently engaged in the development of dry-etch process and research of etch market. Mr. Enami is a member of the Japan Society of Applied Physics.

Masamichi Sakaguchi

Joined Hitachi, Ltd. in 1989, and now works at the Etching Process Design Department, Kasado Division, Nanotechnology Products Business Group, Hitachi High-Technologies Corporation. He is currently engaged in the development of dry-etching system and process.

Naoshi Itabashi

Joined Hitachi, Ltd. in 1992, and now works at the Advanced Technology Research Department, Solution LSI Research Laboratory, Central Research Laboratory. He is currently engaged in the development of dry-etching system and process. Mr. Itabashi is a member of the Japan Society of Applied Physics.

Masaru Izawa

Joined Hitachi, Ltd. in 1989, and now works at the Advanced Technology Research Department, Solution LSI Research Laboratory, Central Research Laboratory. He is currently engaged in the development of dry-etching system and process, and research and development of process control technology. Mr. Izawa is a member of the Japan Society of Applied Physics, and the Chemical Society of Japan.